semiconductor layer;

a color filter layer overlapping only edge portions of the source and the drain electrodes;

a planarization layer over the color filter layer and the source and the drain electrodes, the planarization layer having an opening exposing the drain electrode thereunder; and

a pixel electrode on the planarization layer and electrically connected with the drain electrode via the opening in the planarization layer.

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6. (Amended) A method of forming liquid crystal display (LCD) device, the method comprising:

forming a substrate;

forming a gate electrode over the substrate;

forming an insulation layer on the gate electrode and the substrate;

forming a semiconductor layer, aligned relative to the gate electrode, on the insulating layer;

forming a source electrode and a drain electrode electrically connected with the semiconductor layer;

forming a color filter layer overlapping only edge portions of the source and the drain electrodes;

forming a planarization layer over the color filter layer and the source and drain electrodes, the planarization layer having an opening exposing the drain electrode thereunder; and

B2 cont'd.

forming a pixel electrode on the planarization layer and electrically connected with the drain electrode via the opening in the planarization layer.

15. (Amended) A liquid crystal display device comprising:

a thin film transistor (TFT) formed on a substrate, including a gate electrode, a source electrode, and a drain electrode;

B3 sub C3

a color filter layer overlapping only edge portions of the source and drain electrodes;

a planarization layer formed on the TFT and on the color filter; and

a pixel electrode formed on the planarization layer and electrically contacting the drain electrode.

B4

17. (Amended) The liquid crystal display device of claim 16, wherein the TFT further includes an etch stopper formed on the silicon layer and between the source and drain electrodes.

21. (Amended) A method of manufacturing a liquid crystal display device, the method comprising:

providing a substrate;

forming a gate electrode on the substrate;

depositing sequentially a gate insulating layer, a pure semiconductor layer and a doped semiconductor layer over the substrate;

etching the pure semiconductor layer and the doped semiconductor layer to form an active layer;

forming a source electrode and a drain electrode on the active layer;

forming a color filter, the color filter overlapping only an edge portion of the source and drain electrodes;

etching a portion of the doped semiconductor layer between the source and drain electrodes to form a channel region of a resulting intermediate structure;

forming a planarization layer over the intermediate structure, the planarization layer including a drain contact hole to expose a portion of the drain electrode; and

forming a pixel electrode on the planarization layer, the pixel electrode electrically contacting the drain electrode via the drain contact hole.

22. (Amended) A method of manufacturing a liquid crystal display device, the method comprising:

providing a substrate, the substrate including first and second regions;

forming a thin film transistor (TFT) on the first region of the substrate, the TFT having a gate electrode, an active layer, and source and drain electrodes;

B5 cont'd. sub C4

forming a color filter on a second region of the substrate, the color filter overlapping only edge portions of the source and drain electrodes;

forming a planarization layer on the TFT and the color filter, the planarization layer including a drain contact hole to expose a portion of the drain electrode; and

forming a pixel electrode on the planarization layer, the pixel electrode electrically contacting the drain electrode via the drain contact hole.